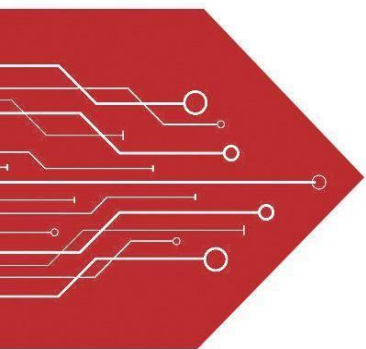


MSKSEMI

SEMICONDUCTOR



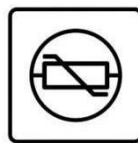
ESD



TVS



TSS



MOV



GDT



PLED

Product data sheet

Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

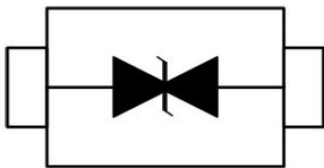
- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Peripherals
- Pagers Peripherals
- Desktop and Servers

Features

- 500W peak pulse power (8/20μs)
- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage:3.3V, 5V, 12V,15, 24V
- Ultra low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: ±30kV
Contact discharge: ±30kV
 - IEC61000-4-4 (EFT) 40A (5/50ns)
- RoHS Compliant



SOT-23



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	500	W
ESD per IEC 61000-4-2 (Air)	VESD	±30	kV
ESD per IEC 61000-4-2 (Contact)		±30	
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

PESD3V3L1BA						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Breakdown Voltage	V _{BR}	4			V	I _T = 1mA
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 5V
Clamping Voltage	V _C		5		V	I _{PP} = 5A (8 x 20μs pulse)
Clamping Voltage	V _C		10		V	I _{PP} = 36A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			18	A	t _p = 8/20μs
Junction Capacitance	C _J			200	pF	V _R = 0V, f = 1MHz

PESD5V0L1BA						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	
Breakdown Voltage	V _{BR}	8.5			V	I _T = 1mA
Reverse Leakage Current	I _R			1	μA	V _{RWM} = 8V
Clamping Voltage	V _C			11	V	I _{PP} = 5A (8 x 20μs pulse)
Clamping Voltage	V _C			15	V	I _{PP} = 34A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			15	A	t _p = 8/20μs
Junction Capacitance	C _J			180	pF	V _R = 0V, f = 1MHz

PESD12VL1BA

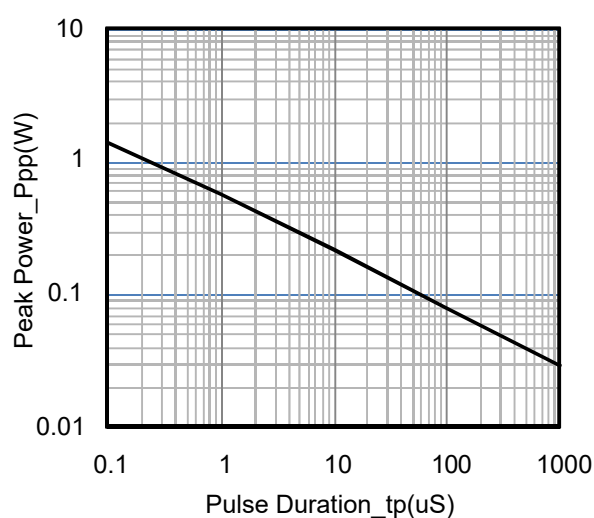
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			12	V	
Breakdown Voltage	VBR	13.3			V	IT = 1mA
Reverse Leakage Current	IR			0.5	μA	VRWM = 12V
Clamping Voltage	VC			19	V	I _{PP} = 5A (8 x 20μs pulse)
Clamping Voltage	VC			28	V	I _{PP} = 18A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			10	A	t _p = 8/20μs
Junction Capacitance	CJ			100	pF	VR = 0V, f = 1MHz

PESD15VL1BA

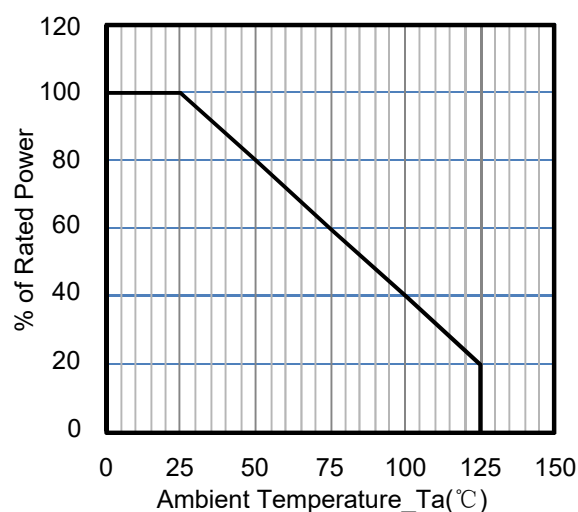
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			15	V	
Breakdown Voltage	VBR	16.7			V	IT = 1mA
Reverse Leakage Current	IR			0.5	μA	VRWM = 12V
Clamping Voltage	VC			19	V	I _{PP} = 5A (8 x 20μs pulse)
Clamping Voltage	VC			28	V	I _{PP} = 18A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			10	A	t _p = 8/20μs
Junction Capacitance	CJ			100	pF	VR = 0V, f = 1MHz

PESD24VL1BA						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			24	V	
Breakdown Voltage	VBR	27			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 24V
Clamping Voltage	VC			40	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	VC			62	V	I _{PP} = 8A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			5	A	tp = 8/20μs
Junction Capacitance	CJ			50	pF	VR = 0V, f = 1MHz

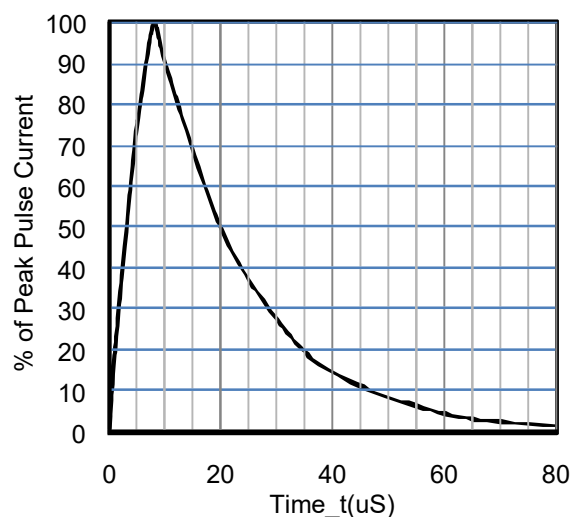
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



Peak Pulse Power vs. Pulse Time

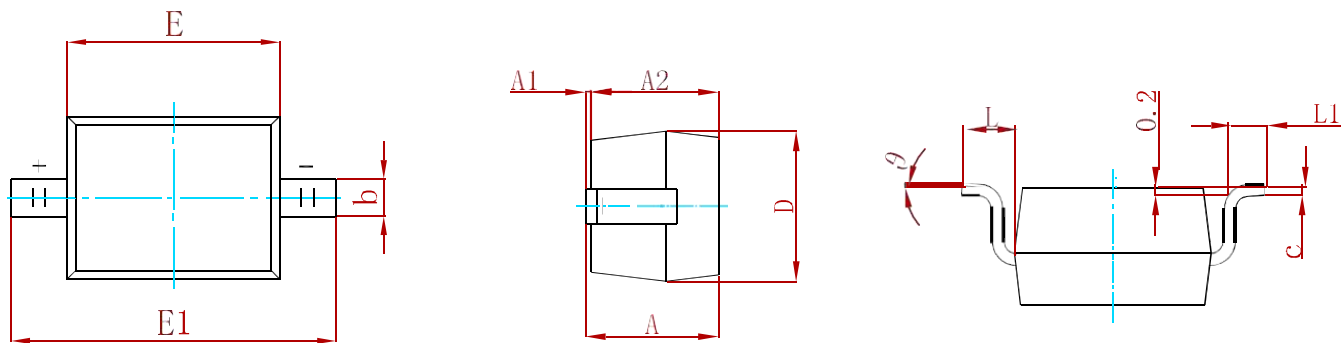


Power Derating Curve



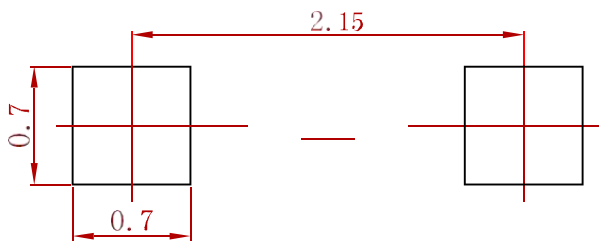
8 X 20uS Pulse Waveform

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

Suggested Pad Layout



- Note:**
- 1.Controlling dimension:in millimeters.
 - 2.General tolerance:± 0.05mm.
 - 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
PESDXXXL1BA	SOD-323	3000

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